

isc Silicon PNP Power Transistors

2SB551

DESCRIPTION

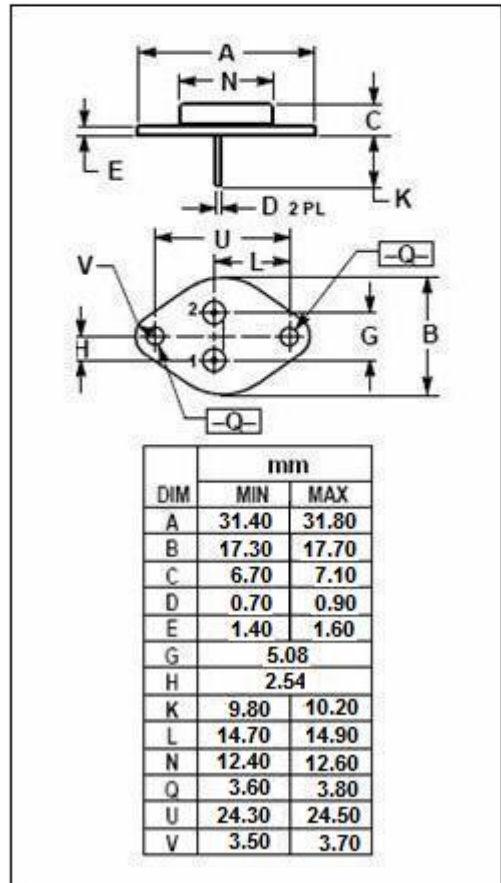
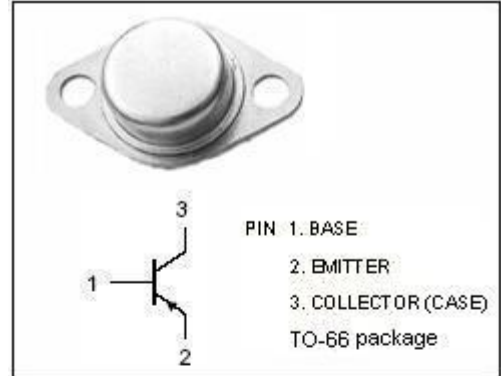
- Low Collector Saturation Voltage-
: $V_{CE(sat)} = -1.2V(Typ.) @ I_C = -2A$
- High Power Dissipation-
: $P_C = 25W(Max) @ T_C = 55^\circ C$

APPLICATIONS

- Designed for low frequency power amplifier applications.

ABSOLUTE MAXIMUM RATINGS($T_a = 25^\circ C$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	-50	V
V_{CEO}	Collector-Emitter Voltage	-50	V
V_{EBO}	Emitter-Base Voltage	-4	V
I_C	Collector Current-Continuous	-3	A
P_C	Collector Power Dissipation @ $T_C = 25^\circ C$	25	W
T_J	Junction Temperature	150	$^\circ C$
T_{stg}	Storage Temperature	-45~150	$^\circ C$



isc Silicon PNP Power Transistors**2SB551****ELECTRICAL CHARACTERISTICS**T_j=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage	I _C = -50mA; R _{BE} = ∞	-50			V
V _{(BR)CBO}	Collector-Base Breakdown Voltage	I _C = -5mA; I _E = 0	-50			V
V _{(BR)EBO}	Emitter-Base Breakdown Voltage	I _E = -5mA; I _C = 0	-4			V
V _{CE(sat)}	Collector-Emitter Saturation Voltage	I _C = -2A; I _B = -0.2A			1.2	V
V _{BE(on)}	Base-Emitter On Voltage	I _C = -1A; V _{CE} = -4V			1.5	V
I _{CBO}	Collector Cutoff Current	V _{CB} = -20V; I _E = 0			-0.1	mA
h _{FE-1}	DC Current Gain	I _C = -1A; V _{CE} = -4V	35		200	
h _{FE-2}	DC Current Gain	I _C = -0.1A; V _{CE} = -4V	35			
f _T	Current-Gain—Bandwidth Product	I _C = -0.5A; V _{CE} = -4V	15			MHz

◆ **h_{FE-1} Classifications**

A	B	C
35-70	60-120	100-200